



Pending

Active

- ☒ L1:(77) (SiO₂ or "SiO₂" or "SiO.sub.2" or "SiO.sub.2" or "SiO.sub.x" or "SiO.sub.x" or "s...
- ☒ L2:(197925) Lee
- ☒ L3:(6) 1 and 2
- ☒ L4:(3372721) @ad<20011022
- ☒ L5:(5) 3 and 4
- ☒ L6:(3) (SiO₂ or "SiO₂" or "SiO.sub.2" or "SiO.sub.2" or "SiO.sub.x" or "SiO.sub.x" or "si...
- ☒ L7:(918022) ratio or ratios
- ☒ L8:(3) 6 and 7
- ☒ L9:(18) (SiO₂ or "SiO₂" or "SiO.sub.2" or "SiO.sub.2" or "SiO.sub.x" or "SiO.sub.x" or "s...
- ☒ L10:(17) 9 not 3
- ☒ L11:(13) 4 and 10
- ☒ L12:(11) 7 and 11
- ☒ L13:(1) ("6291030").PN.
- ☒ L14:(202774) etch\$
- ☒ L15:(1) 13 and 14
- ☒ L16:(296473) He or helium
- ☒ L17:(0) 13 and 16
- ☒ L18:(1) ("6211040").PN.
- ☒ L19:(0) 16 and 18
- ☒ L20:(5) 12 and 16
- ☒ L21:(66082) 438/\$7.ccls.
- ☒ L22:(117480) 257/\$7.ccls.
- ☒ L23:(138713) 21 or 22
- ☒ [REDACTED]

Failed

Document ID	Issue Dat	Page	Title	Current O	Current XR	Retrieval	Inventor	SIC P

Ready

L Number	Hits	Search Text	DB	Time stamp
1	77	(SiO2 or "Si O2" or "SiO.sub.2" or "Si O.sub.2" or "SiO.sub.x" or "Si O.sub.x" or "silicon dioxide" or "silicon-dioxide") with (oxygen or "O.sub.2") with (silane or "SiH4" or "Si H4" or "SiH.sub.4" or "Si H.sub.4") with (ratio or ratios)	USPAT; US-PGPUB	2003/06/07 20:56
2	197925	Lee	USPAT; US-PGPUB	2003/06/07 18:37
3	6	((SiO2 or "Si O2" or "SiO.sub.2" or "Si O.sub.2" or "SiO.sub.x" or "Si O.sub.x" or "silicon dioxide" or "silicon-dioxide") with (oxygen or "O.sub.2") with (silane or "SiH4" or "Si H4" or "SiH.sub.4" or "Si H.sub.4") with (ratio or ratios)) and Lee	USPAT; US-PGPUB	2003/06/07 18:38
4	3372721	@ad<20011022	USPAT; US-PGPUB	2003/06/07 18:38
5	5	((((SiO2 or "Si O2" or "SiO.sub.2" or "Si O.sub.2" or "SiO.sub.x" or "Si O.sub.x" or "silicon dioxide" or "silicon-dioxide") with (oxygen or "O.sub.2") with (silane or "SiH4" or "Si H4" or "SiH.sub.4" or "Si H.sub.4") with (ratio or ratios)) and Lee) and @ad<20011022	USPAT; US-PGPUB	2003/06/07 18:38
6	3	(SiO2 or "Si O2" or "SiO.sub.2" or "Si O.sub.2" or "SiO.sub.x" or "Si O.sub.x" or "silicon dioxide" or "silicon-dioxide") with (oxygen or "O.sub.2") with (silane or "SiH4" or "Si H4" or "SiH.sub.4" or "Si H.sub.4") with (ratio or ratios) with (HDPCVD or "HDP CVD" or "HDP-CVD" or "high density plasma CVD" or "high-density-plasma CVD" or "high density plasma-CVD" or "high-density-plasma-CVD" or "HDP chemical vapor deposition" or "HDP chemical-vapor-deposition" or "HDP-chemical vapor deposition" or "HDP-chemical-vapor-deposition" or "high density plasma chemical vapor deposition" or "high density plasma-chemical vapor deposition" or "high-density-plasma chemical-vapor-deposition" or "high-density-plasma-chemical-vapor-deposition")	USPAT; US-PGPUB	2003/06/07 21:00
7	918022	ratio or ratios	USPAT; US-PGPUB	2003/06/07 19:29

8	3	((SiO ₂ or "Si O ₂ " or "SiO.sub.2" or "Si O.sub.2" or "SiO.sub.x" or "Si O.sub.x" or "silicon dioxide" or "silicon-dioxide") with (oxygen or "O.sub.2") with (silane or "SiH ₄ " or "Si H ₄ " or "SiH.sub.4" or "Si H.sub.4") with (ratio or ratios) with (HDPCVD or "HDP CVD" or "HDP-CVD" or "high density plasma CVD" or "high-density-plasma CVD" or "high density plasma-CVD" or "high-density-plasma-CVD" or "HDP chemical vapor deposition" or "HDP chemical-vapor-deposition" or "HDP-chemical vapor deposition" or "HDP-chemical-vapor-deposition" or "high density plasma chemical vapor deposition" or "high density plasma-chemical vapor deposition" or "high-density-plasma chemical-vapor-deposition" or "high-density-plasma-chemical-vapor-deposition")) and (ratio or ratios)	USPAT; US-PGPUB	2003/06/07 19:29
9	18	(SiO ₂ or "Si O ₂ " or "SiO.sub.2" or "Si O.sub.2" or "SiO.sub.x" or "Si O.sub.x" or "silicon dioxide" or "silicon-dioxide") with (oxygen or "O.sub.2") with (silane or "SiH ₄ " or "Si H ₄ " or "SiH.sub.4" or "Si H.sub.4") with (HDPCVD or "HDP CVD" or "HDP-CVD" or "high density plasma CVD" or "high-density-plasma CVD" or "high density plasma-CVD" or "high-density-plasma-CVD" or "HDP chemical vapor deposition" or "HDP chemical-vapor-deposition" or "HDP-chemical vapor deposition" or "HDP-chemical-vapor-deposition" or "high density plasma chemical vapor deposition" or "high density plasma-chemical vapor deposition" or "high-density-plasma chemical-vapor-deposition" or "high-density-plasma-chemical-vapor-deposition")	USPAT; US-PGPUB	2003/06/07 21:01

10	17	((SiO2 or "Si O2" or "SiO.sub.2" or "Si O.sub.2" or "SiO.sub.x" or "Si O.sub.x" or "silicon dioxide" or "silicon-dioxide") with (oxygen or "O.sub.2") with (silane or "SiH4" or "Si H4" or "SiH.sub.4" or "Si H.sub.4") with (HDPCVD or "HDP CVD" or "HDP-CVD" or "high density plasma CVD" or "high-density-plasma CVD" or "high density plasma-CVD" or "high-density-plasma-CVD" or "HDP chemical vapor deposition" or "HDP chemical-vapor-deposition" or "HDP-chemical vapor deposition" or "HDP-chemical-vapor-deposition" or "high density plasma chemical vapor deposition" or "high density plasma-chemical vapor deposition" or "high-density-plasma chemical-vapor-deposition" or "high-density-plasma-chemical-vapor-deposition")) not (((SiO2 or "Si O2" or "SiO.sub.2" or "Si O.sub.2" or "SiO.sub.x" or "Si O.sub.x" or "silicon dioxide" or "silicon-dioxide") with (oxygen or "O.sub.2") with (silane or "SiH4" or "Si H4" or "SiH.sub.4" or "Si H.sub.4") with (ratio or ratios)) and Lee)	USPAT; US-PGPUB	2003/06/07 21:01
11	13	@ad<20011022 and (((SiO2 or "Si O2" or "SiO.sub.2" or "Si O.sub.2" or "SiO.sub.x" or "Si O.sub.x" or "silicon dioxide" or "silicon-dioxide") with (oxygen or "O.sub.2") with (silane or "SiH4" or "Si H4" or "SiH.sub.4" or "Si H.sub.4") with (HDPCVD or "HDP CVD" or "HDP-CVD" or "high density plasma CVD" or "high-density-plasma CVD" or "high density plasma-CVD" or "high-density-plasma-CVD" or "HDP chemical vapor deposition" or "HDP chemical-vapor-deposition" or "HDP-chemical vapor deposition" or "HDP-chemical-vapor-deposition" or "high density plasma chemical vapor deposition" or "high density plasma-chemical vapor deposition" or "high-density-plasma chemical-vapor-deposition" or "high-density-plasma-chemical-vapor-deposition")) not (((SiO2 or "Si O2" or "SiO.sub.2" or "Si O.sub.2" or "SiO.sub.x" or "Si O.sub.x" or "silicon dioxide" or "silicon-dioxide") with (oxygen or "O.sub.2") with (silane or "SiH4" or "Si H4" or "SiH.sub.4" or "Si H.sub.4") with (ratio or ratios)) and Lee))	USPAT; US-PGPUB	2003/06/07 21:01

12	11	(ratio or ratios) and (@ad<20011022 and (((SiO2 or "SiO2" or "SiO.sub.2" or "SiO.sub.2" or "SiO.sub.x" or "SiO.sub.x" or "silicon dioxide" or "silicon-dioxide") with (oxygen or "O.sub.2") with (silane or "SiH4" or "SiH4" or "SiH.sub.4" or "SiH.sub.4") with (HDPCVD or "HDPCVD" or "HDP-CVD" or "high density plasma CVD" or "high-density-plasma CVD" or "high density plasma-CVD" or "high-density-plasma-CVD" or "HDP chemical vapor deposition" or "HDP chemical-vapor-deposition" or "HDP-chemical vapor deposition" or "HDP-chemical-vapor-deposition" or "high density plasma chemical vapor deposition" or "high density plasma-chemical vapor deposition" or "high-density-plasma chemical-vapor-deposition" or "high-density-plasma-chemical-vapor-deposition"))) not (((SiO2 or "SiO2" or "SiO.sub.2" or "SiO.sub.2" or "SiO.sub.x" or "SiO.sub.x" or "silicon dioxide" or "silicon-dioxide") with (oxygen or "O.sub.2") with (silane or "SiH4" or "SiH4" or "SiH.sub.4" or "SiH.sub.4") with (ratio or ratios)) and Lee)))	USPAT; US-PGPUB	2003/06/07 21:47
13	1	("6291030").PN.	USPAT; US-PGPUB	2003/06/07 21:47
14	202774	etch\$	USPAT; US-PGPUB	2003/06/07 21:47
15	1	((("6291030").PN.) and etch\$	USPAT; US-PGPUB	2003/06/07 22:07
16	296473	He or helium	USPAT; US-PGPUB	2003/06/07 22:07
17	0	((("6291030").PN.) and (He or helium)	USPAT; US-PGPUB	2003/06/07 22:08
18	1	("6211040").PN.	USPAT; US-PGPUB	2003/06/07 22:08
19	0	(He or helium) and ((("6211040").PN.)	USPAT; US-PGPUB	2003/06/07 22:08

20	5	((ratio or ratios) and (@ad<20011022 and (((SiO2 or "Si O2" or "SiO.sub.2" or "Si O.sub.2" or "SiO.sub.x" or "Si O.sub.x" or "silicon dioxide" or "silicon-dioxide") with (oxygen or "O.sub.2") with (silane or "SiH4" or "Si H4" or "SiH.sub.4" or "Si H.sub.4") with (HDPCVD or "HDP CVD" or "HDP-CVD" or "high density plasma CVD" or "high-density-plasma CVD" or "high density plasma-CVD" or "high-density-plasma-CVD" or "HDP chemical vapor deposition" or "HDP chemical-vapor-deposition" or "HDP-chemical vapor deposition" or "HDP-chemical-vapor-deposition" or "high density plasma chemical vapor deposition" or "high density plasma-chemical vapor deposition" or "high-density-plasma chemical-vapor-deposition" or "high-density-plasma-chemical-vapor-deposition")) not (((SiO2 or "Si O2" or "SiO.sub.2" or "Si O.sub.2" or "SiO.sub.x" or "Si O.sub.x" or "silicon dioxide" or "silicon-dioxide") with (oxygen or "O.sub.2") with (silane or "SiH4" or "Si H4" or "SiH.sub.4" or "Si H.sub.4") with (ratio or ratios)) and Lcc)))) and (He or helium)	USPAT; US-PGPUB	2003/06/07 22:22
21	66082	438/\$7.ccls.	USPAT; US-PGPUB	2003/06/07 22:22
22	117480	257/\$7.ccls.	USPAT; US-PGPUB	2003/06/07 22:23
23	138713	438/\$7.ccls. or 257/\$7.ccls.	USPAT; US-PGPUB	2003/06/07 22:23
24	18	((SiO2 or "Si O2" or "SiO.sub.2" or "Si O.sub.2" or "SiO.sub.x" or "Si O.sub.x" or "silicon dioxide" or "silicon-dioxide") with (oxygen or "O.sub.2") with (silane or "SiH4" or "Si H4" or "SiH.sub.4" or "Si H.sub.4") with (HDPCVD or "HDP CVD" or "HDP-CVD" or "high density plasma CVD" or "high-density-plasma CVD" or "high density plasma-CVD" or "high-density-plasma-CVD" or "HDP chemical vapor deposition" or "HDP chemical-vapor-deposition" or "HDP-chemical vapor deposition" or "HDP-chemical-vapor-deposition" or "high density plasma chemical vapor deposition" or "high density plasma-chemical vapor deposition" or "high-density-plasma chemical-vapor-deposition" or "high-density-plasma-chemical-vapor-deposition")) and (438/\$7.ccls. or 257/\$7.ccls.)	USPAT; US-PGPUB	2003/06/07 22:23